

T-37-17

**1.8W PNP GENERAL PURPOSE
SMALL SIGNAL TRANSISTORS**

**2N2906
2N2907**

These transistors are silicon planar epitaxial pnp devices conforming to JEDEC TO-18, BS SO-132A and IEC C7/B11 outlines.

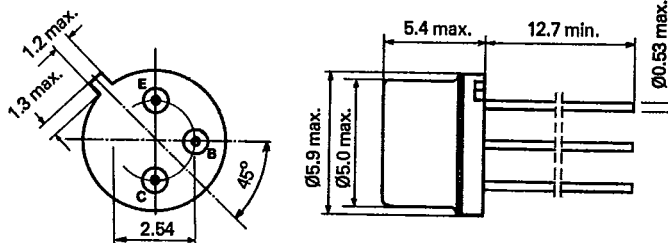
They are designed for high speed saturated switching and general purpose applications.

QUICK REFERENCE DATA

	2N2906	2N2907
V _{CB0} max.		60V
V _{CE0} max.		40V
V _{CE(sat)} max. at I _C = 500mA, I _B = 50mA and T _{amb} = 25°C		1.6V
I _C max.		600mA
h _{FE} min. at V _{CE} = 10V, I _C = 150mA and T _{amb} = 25°C	40	100
P _{tot} max. at T _{amb} = 25°C		0.4W

Outline and Dimensions

JEDEC TO-18
BS SO-132A
IEC C7/B11



All dimensions in millimetres
For detail dimensions see Page 4

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In the interest of improved product design, changes to this specification may be made at any time.



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RATINGS 81C 00120 D

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The ratings quoted are limiting values of operating and environmental conditions and are in accordance with the absolute maximum rating system defined in BS 3494 (Part 1) and IEC Publication 134.

Voltage Ratings

V _{CB0}	Collector-base voltage at I _E = 0	60V
V _{CE0}	Collector-emitter voltage at I _B = 0	40V
V _{EBO}	Emitter-base voltage at I _C = 0	5V

Current Rating

I _C	Collector current (continuous)	600mA
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Power Ratings

P _{tot}	Total power dissipation	
	T _{amb} = 25°C	0.4W
	T _{case} = 25°C	1.8W

Thermal Ratings

T _j	Operating junction temperature range	-65°C to +200°C
T _{stg}	Storage temperature range	-65°C to +200°C

CHARACTERISTICS**Electrical Characteristics**

		Min.	Typ.	Max.
I _{CB0}	Collector-base cut-off current V _{CB} = 50V, I _E = 0 and T _{amb} = 25°C V _{CB} = 50V, I _E = 0 and T _{amb} = 150°C			20nA 20μA
I _{CEX}	Collector-emitter cut-off current at V _{CE} = 30V, V _{BE} = 0.5V and T _{amb} = 25°C			50nA
I _{BEX}	Base-emitter cut-off current at V _{BE} = 0.5V, V _{CE} = 30V and T _{amb} = 25°C			50nA
V _{CB0}	Collector-base voltage at I _C = 10μA, I _E = 0 and T _{amb} = 25°C	60V		
V _{CE0(sus)}	*Collector-emitter sustaining voltage at I _C = 10mA, I _B = 0 and T _{amb} = 25°C	40V		
V _{EBO}	Emitter-base voltage at I _C = 0, I _E = 10μA and T _{amb} = 25°C	5V		
V _{BE(sat)}	*Base-emitter saturation voltage I _C = 150mA, I _B = 15mA and T _{amb} = 25°C I _C = 500mA, I _B = 50mA and T _{amb} = 25°C			1.3V 2.6V
V _{CE(sat)}	*Collector-emitter saturation voltage I _C = 150mA, I _B = 15mA and T _{amb} = 25°C I _C = 500mA, I _B = 50mA and T _{amb} = 25°C			0.4V 1.6V

**1.8W PNP GENERAL PURPOSE
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2N2907

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Electrical Characteristics (continued)

		Min.	Typ.	Max.	
h _{FE}	Static value of common emitter forward current transfer ratio V _{CE} = 10V, I _C = 0.1mA and T _{amb} = 25°C				
		2N2906	20		
		2N2907	35		
		V _{CE} = 10V, I _C = 1.0mA and T _{amb} = 25°C			
		2N2906	25		
		2N2907	50		
		V _{CE} = 10V, I _C = 10mA and T _{amb} = 25°C			
		2N2906	35		
		2N2907	75		
		V _{CE} = 10V, I _C = 150mA* and T _{amb} = 25°C			
		2N2906	40	120	
		2N2907	100	300	
V _{CE} = 10V, I _C = 500mA* and T _{amb} = 25°C					
2N2906	20				
2N2907	30				
f _T	Transition frequency at V _{CE} = 20V, I _C = 50mA, f = 100MHz and T _{amb} = 25°C		200MHz		
C _{EBO}	Emitter-base capacitance at V _{EB} = 2V, I _C = 0, f = 100 kHz and T _{amb} = 25°C			30pF	
C _{CB0}	Collector-base capacitance at V _{CB} = 10V, I _E = 0, f = 100 kHz and T _{amb} = 25°C			8pF	

*Pulsed; t_p = 300 μs; duty cycle 1%

Switching Times

(I_C = 150mA, I_{B1} = -I_{B2} = 15mA, V_{CC} = 30V (t_d and t_r) or 6V (t_s and t_f) and T_{amb} = 25°C)

		Min.	Typ.	Max.
t _d	Delay time			10ns
t _r	Rise time			40ns
t _s	Storage time			80ns
t _f	Fall time			30ns

Thermal Characteristics

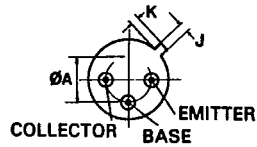
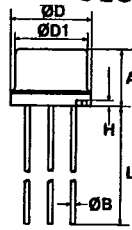
		Min.	Typ.	Max.
R _{th(j-case)}	Thermal resistance (junction to case)			97.3 deg C/W
R _{th(j-amb)}	Thermal resistance (junction to ambient)			437.5 deg C/W

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MECHANICAL DETAILS
Outline and Dimensions

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Ref.	Millimetres		Inches		Notes
	Min.	Max.	Min.	Max.	
A	4.32	5.33	0.170	0.210	
ØA	2.54 nom.		0.100 nom.		
ØB	0.41	0.53	0.016	0.021	
ØD	5.31	5.84	0.209	0.230	
ØD1	4.52	4.95	0.178	0.195	
H	0.13	0.76	0.005	0.030	
J	0.92	1.16	0.036	0.046	
K	0.71	1.21	0.028	0.048	
L	12.7	—	0.500	—	

Notes

- The transistors conform to BS SO-132A, IEC C7/B11 and JEDEC TO-18 outlines.
- The millimetre dimensions are derived from the inch dimensions.

Weight 0.3 gramme.

INSTALLATION NOTES

The emitter, base and collector leads are identified on the transistor outline.
 Note the collector is connected also to the case.

The leads must not be bent within 0.06in (1.5mm) of the seals.

When soldering, a thermal shunt should be used to protect the transistor.

The transistor leads may be dip-soldered at a temperature of 240°C for 10 seconds up to a point 0.04in (1mm) from the seals.

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